

**IN THE CLAIMS:**

1. (Previously Presented) A semiconductor light emitting device comprising:

a multilayer epitaxial structure including a first conductive layer, a second conductive layer, and a light emitting layer between the first conductive layer and the second conductive layer, a main surface of the second conductive layer which faces away from the light emitting layer being a light extraction surface;

5 a first electrode formed on a main surface of the first conductive layer which faces away from the light emitting layer;

a second electrode formed on the main surface of the second conductive layer which faces away from the light emitting layer;

10 a first power supply terminal that is electrically connected to the first electrode and forms at least part of a metal layer, the multilayer epitaxial structure being formed on the metal layer in such a manner that the first conductive layer is closer to the metal layer than the second conductive layer is, the metal layer supporting the multilayer epitaxial structure, and conducting heat generated in the light emitting layer; and

15 a second power supply terminal that is electrically connected to the second electrode by means of a conductive member which extends from the second electrode in a direction parallel to the main surface of the second conductive layer,

wherein the second power supply terminal forms a conductive film on a surface of the metal layer on which the multilayer epitaxial structure is formed, and an insulating film is 20 formed between the second power supply terminal and the surface of the metal layer.

2. (Original) The semiconductor light emitting device of Claim 1, wherein  
the metal layer is electrically divided into at least two portions, and  
at least one of the portions is constituted as the first power supply terminal, and at  
least one of a rest of the portions is connected to the second electrode, to be constituted as the  
5 second power supply terminal.

3. (Cancelled)

4. (Previously Presented) The semiconductor light emitting device of Claim 1,  
wherein  
the first power supply terminal forms the entire metal layer.

5. (Previously Presented) The semiconductor light emitting device of Claim 1,  
wherein

the conductive film is formed so as to surround the multilayer epitaxial structure,  
and is also constituted as a light-reflective film.

6. (Original) The semiconductor light emitting device of Claim 1, wherein  
the first electrode is formed on substantially the entire main surface of the first  
conductive layer which faces away from the light emitting layer, and reflects light emitted from  
the light emitting layer.

7. (Original) The semiconductor light emitting device of Claim 1, wherein  
the second electrode is a transparent electrode which transmits the light emitted  
from the light emitting layer.

8. (Original) The semiconductor light emitting device of Claim 7, wherein  
the second electrode is formed on substantially the entire main surface of the  
second conductive layer which faces away from the light emitting layer.

9. (Original) The semiconductor light emitting device of Claim 1, further  
comprising:

a phosphor layer formed on the multilayer epitaxial structure so as to cover the  
main surface of the second conductive layer which faces away from the light emitting layer, the  
5 phosphor layer including a light emitting substance which is excited by the light emitted from the  
light emitting layer, to emit light.

10. (Original) The semiconductor light emitting device of Claim 1, wherein  
each of the first conductive layer, the light emitting layer, and the second  
conducting layer is made of a compound semiconductor including nitrogen.

11.-16. (Cancelled)

17. (Previously Presented) A lighting module comprising:  
a printed wiring board including a bonding pad; and;  
a semiconductor light emitting device as defined in Claim 1, the semiconductor  
light emitting device being mounted on the printed wiring board by connecting a metal layer  
5 included in the semiconductor light emitting device to the bonding pad.

18. (Original) A lighting apparatus comprising a lighting module as defined in Claim  
17.

19.-28. (Cancelled)

29. (Previously Presented) The semiconductor light emitting device of Claim 2,  
wherein

the first power supply terminal forms the entire metal layer.

30. (Previously Presented) The semiconductor light emitting device of Claim 2,  
wherein

the conductive film is formed so as to surround the multilayer epitaxial structure,  
and is also constituted as a light-reflective film.

31. (Previously Presented) The semiconductor light emitting device of Claim 2,  
wherein

the first electrode is formed on substantially the entire main surface of the first  
conductive layer which faces away from the light emitting layer, and reflects light emitted from  
5 the light emitting layer.

32. (Previously Presented) The semiconductor light emitting device of Claim 2,  
wherein

the second electrode is a transparent electrode which transmits the light emitted  
from the light emitting layer.

33. (Previously Presented) The semiconductor light emitting device of Claim 32,  
wherein

the second electrode is formed on substantially the entire main surface of the second conductive layer which faces away from the light emitting layer.

34. (Previously Presented) The semiconductor light emitting device of Claim 2, further comprising:

a phosphor layer formed on the multilayer epitaxial structure so as to cover the main surface of the second conductive layer which faces away from the light emitting layer, the 5 phosphor layer including a light emitting substance which is excited by the light emitted from the light emitting layer, to emit light.

35. (Previously Presented) The semiconductor light emitting device of Claim 2, wherein

each of the first conductive layer, the light emitting layer, and the second conductive layer is made of a compound semiconductor including nitrogen.

36. (Previously Presented) A lighting module comprising:

a printed wiring board including a bonding pad; and

a semiconductor light emitting device as defined in Claim 2, the semiconductor light emitting device being mounted on the printed wiring board by connecting a metal layer 5 included in the semiconductor light emitting device to the bonding pad.

37. (Previously Presented) A lighting apparatus comprising a lighting module as defined in Claim 36.

38.-39. (Cancelled)